

Supporting Information for

Nonlinear Optical ASnX (A = Na, H; X = N, P) Nanosheets with Divalent Tin Lone Electron Pair Effect by First-Principles Design

Shengzi Zhang,^{ac} Lei Kang^{*a} and Zheshuai Lin^{*ab}

^a Technical Institute of Physics and Chemistry, Chinese Academy of Sciences, Beijing 100190, China

^b Center of Materials Science and Optoelectronics Engineering, University of Chinese Academy of Sciences, Beijing 100049, China

^c University of Chinese Academy of Sciences, Beijing 100049, China

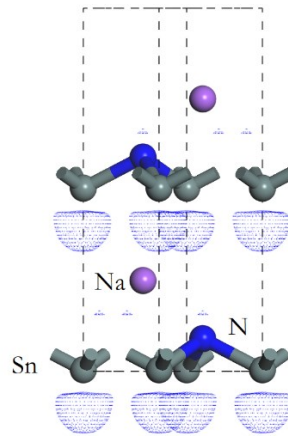
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1. **Table S1** Experimental and calculated crystallographic data of ZnGeP₂ and NaSnX (X = N, P). It can be found that the LDA results are sufficiently accurate for the calculations of lattice constants.

		a=b (Å)	(relative error)	c (Å)	(relative error)
ZnGeP ₂	Exp.	5.465		10.711	
	Cal. by LDA	5.387	(-1.4%)	10.496	(-2.0%)
	Cal. by sX-LDA	5.270	(-3.6%)	10.342	(-3.4%)
NaSnN	Exp.	3.331		10.892	
	Cal. by LDA	3.201	(-3.9%)	10.773	(-1.1%)
	Cal. by sX-LDA	3.176	(-4.7%)	10.774	(-1.1%)
NaSnP	Exp.	3.880		11.667	
	Cal. by LDA	3.775	(-2.7%)	11.602	(-0.6%)
	Cal. by sX-LDA	3.795	(-2.2%)	11.664	(-0.0%)

2. **Figure S1.** First-principles analysis of electron localization function (ELF) for NaSnN.



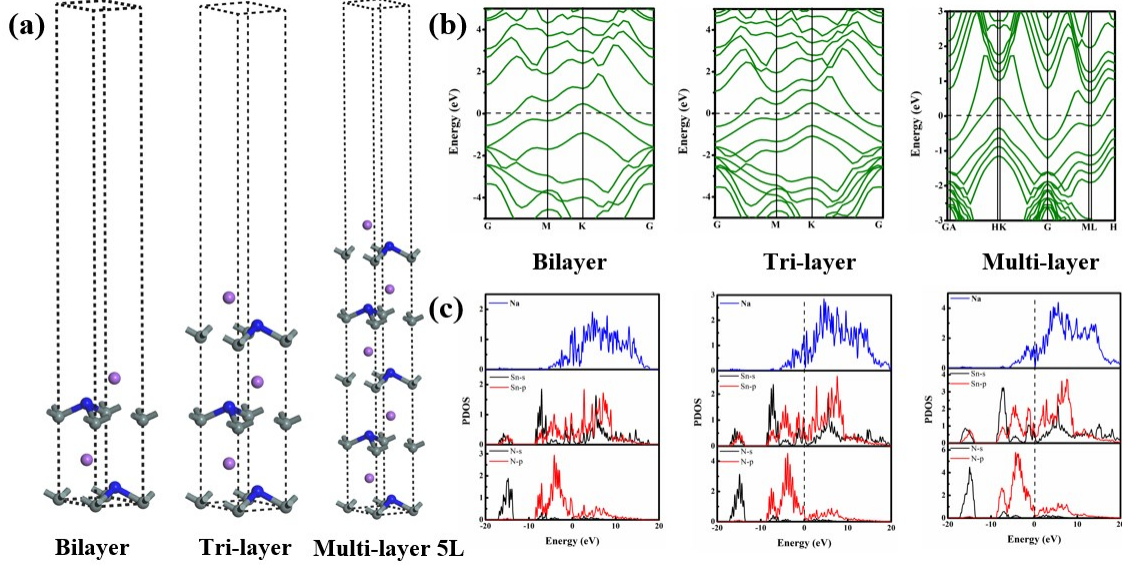
3. **Table S2.** Detailed VE and VH contribution to the total SHG coefficient d_{ijk} as shown in Figure 3.

System		d_{ijk} (pm/V)	VE (pm/V)	VH (pm/V)
NaSnN	Bulk	Cal. $d_{333}=27$	$d_{333}=18$	$d_{333}=9.4$
HSnN	ML	Cal. $d_{111}=147$	$d_{111}=256$	$d_{111}=-108$
NaSnN	ML ^{a)}	Cal. $d_{113}=301$; $d_{333}=277$	$d_{113}=259$; $d_{333}=395$	$d_{113}=42$; $d_{333}=-118$
NaSnP	Bulk	Cal. $d_{333}=16$	$d_{333}=6.7$	$d_{333}=9.7$
NaSnP	ML	Cal. $d_{113}=618$; $d_{333}=533$	$d_{113}=565$; $d_{333}=662$	$d_{113}=54$; $d_{333}=-130$
HSnP	ML	Cal. $d_{111}=12$; $d_{333}=-14$	$d_{111}=43$; $d_{333}=-9.4$	$d_{111}=-31$; $d_{333}=-4.8$

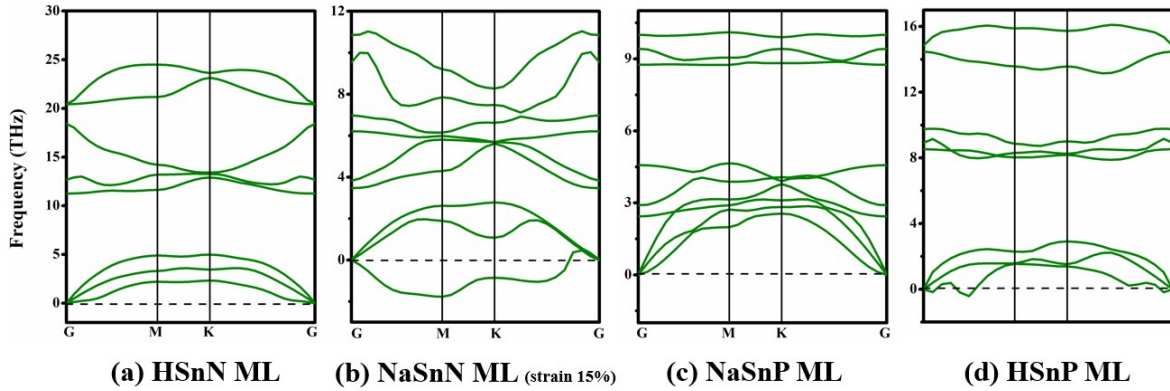
^{a)} strain is 15%

4. **Figure S2.** Crystal structures (a), band structures (b) and PDOS (c) of the NaSnN bilayer, tri-layer and

multi-layer (e.g., 5L)



5. **Figure S3.** Phonon vibration spectra of HSnn monolayer (ML) (a), 15%-strained NaSnN ML (b), NaSnP ML (c) and HSnP ML (d).



6. **Figure S4.** Interaction energies of HSnn, NaSnP and MoS₂ with respect to the interlayer distance.

